F. Silicon Device and Integration Technology 분과

Room G

하나스퀘어 (B112)

일 시 : 2월 16일(목) 11:20-12:35

세션명 : [TG2-F] Integration Technology for Advance Materials and Devices

좌 장 : 이석희(KAIST), 이병훈(광주과학기술원)

TG2-F-1 11:20-11:35 Effect of SC1 Cleaning on the Performance of Graphene FET

저자: 박은지[1], 강창구[2], 이상경[2], 조천흠[1], 이영곤[2], 정현종[3], 서순애[4], 이병훈[1,2]

소속: [1]광주과학기술원 나노바이오 전자재료공학과, [2]광주과학기술원 신소재공학부, [3]삼성종합기술원, [4]세종대학교 물리학과

TG2-F-2 11:35-11:50 Wafer-scale Graphene Nanoribbons for Tunnel FET Applications

저자: W. S. Hwang[1], K. Tahy[1], P. Zhao[1], R. L. Myers-Ward[2], P. M. Campbell[2], C. R Eddy[2], Jr., D. K. Gaskill[2], H. Xing[1], A. C. Seabaugh[1], and D. Jena[1]

소속: [1]Department of Electrical Engineering, University of Notre Dame, [2]U. S. Naval Research Laboratory

TG2-F-3 11:50-12:05 The Improvement of Device Characteristic in HK/MG Logic Device by Newly Developed CESL

저자: Hyunkwan Yu, Yong-kuk Jeong, Pankwi Park, Ki-Eun Kim, Sang-Uk Park, Dong Suk Shin, Moon Han Park, Ja-Hm Ku, and Nae-In Lee

소속: Advanced Process Development / TD, System LSI Division, Samsung Electronics Co., Ltd.

TG2-F-4 12:05-12:20 The Effect of Thermal Budget on the Insulating Properties of HfO_2 on Ge Substrate

저자: Hyung-Suk Jung[1], Il-Hyuk Yu[1], Hyo Kyeom Kim[1], Sang Young Lee[1], Tae Joo Park[2], Nae-In Lee[3], and Cheol Seong Hwang[1]

소속: [1]WCU Hybrid Materials Program, Department of Materials Science and Engineering and Inter-university Semiconductor Research Center, Seoul National University, [2]Hanyang University, [3]SYS LSI division, Samsung Electronics Co., Ltd.

TG2-F-5 12:20-12:35 Ground-plane Doping for V_T-modulation of Planar Tunnel Field-effect Transistors on Ultra-thin-body and BOX (UTBB) SOI Substrate

저자: M.-C. Sun[1,2], H. Kim[1], S. W. Kim[1], G. Kim[1], H. W. Kim[1], J.-H. Lee[1], H. Shin[1], and B.-G. Park[1]

소속: [1]Inter-university Semiconductor Research Center and School of Electrical Engineering and Computer Science, Seoul National University, [2]TD (S. LSI), Semiconductor Business Group, Samsung Electronics Co., Ltd.